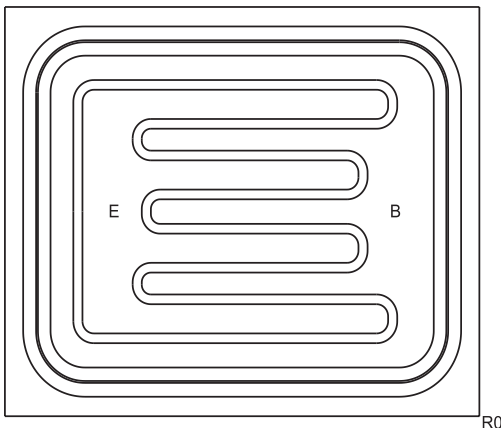


PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 X 99 MILS
Die Thickness	12.5 ± 1 MILS
Base Bonding Pad Area	12 X 32 MILS
Emitter Bonding Pad Area	13 X 46 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Cr/Ni/Ag - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

1,450

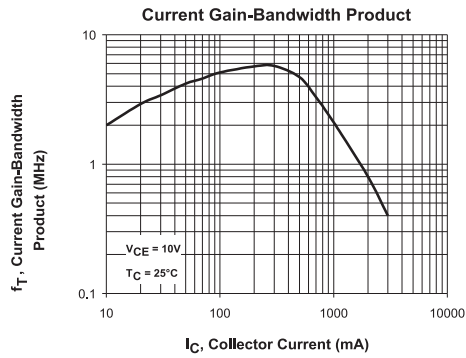
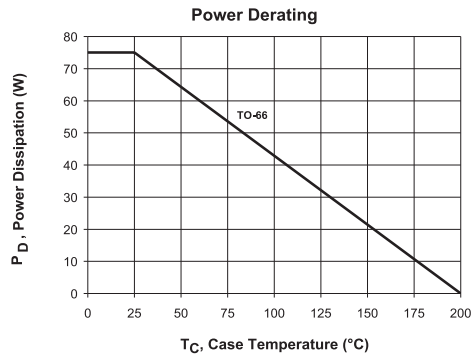
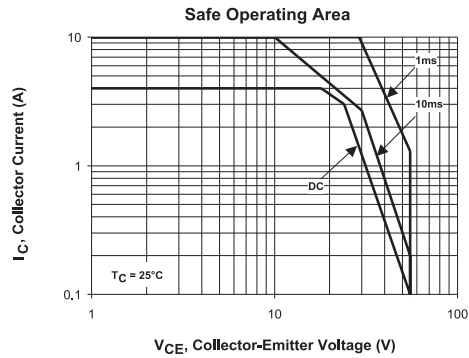
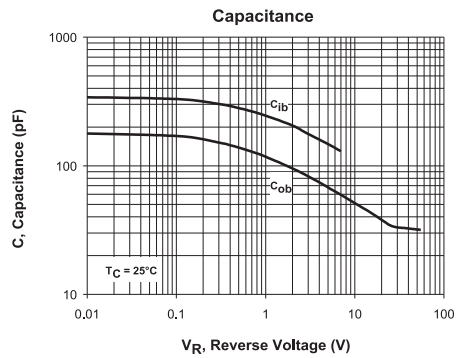
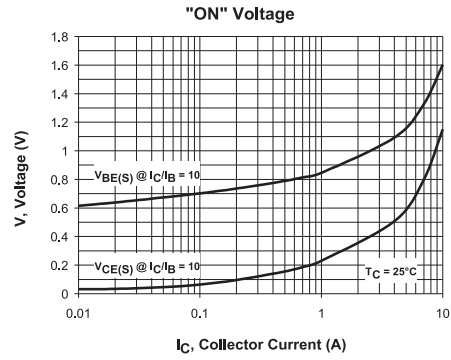
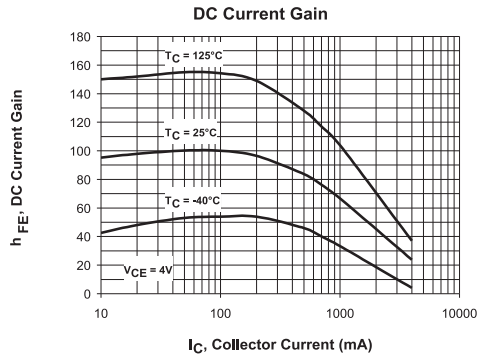
PRINCIPAL DEVICE TYPES

CJD42C

TIP42C

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